Please replace paragraph [0010] with the following amended paragraph:

[0010] The p-type nitride semiconductor layer 500 is doped with an impurity such as Mg, and has a p-type conductivity through an activation process. U.S. Patent No.5,247,533 discloses a technology in which a p-type nitride semiconductor layer is activated by means of irradiation of electron beam. U.S. Patent No.5,306,662 discloses a technology in which a p-type nitride semiconductor layer is activated through annealing at a temperature of 400°C or more. Korean Patent No.10-043346 10-0432246 discloses a technology in which NH3 and a hydrazine-based source material are used together as a nitrogen precursor for growing a p-type nitride semiconductor layer, so that the p-type nitride semiconductor layer has a p-type conductivity without an activation process.

Please replace paragraph [0014] with the following amended paragraph:

[0014] A variety of methods have been proposed in order to reduce the contact resistance between the p-type GaN used as the p-type nitride semiconductor layer 500 and the p-side electrode 600. Among them, there is a method in which the p-type nitride semiconductor layer 500 is not made of a single p-type GaN layer, but is formed to have a superlattice structure of p-type GaN/p-type InGaN or p-type GaN/p-type AlGaN, and the concentration of holes, which is significantly higher than the concentration that can be obtained in the single p-type GaN layer, is thus obtained within the superlattice structure through piezoelectric field. This method, however, is not preferred [[that]] because potential barrier is formed in a vertical direction within the superlattice structure before holes are injected into the active layer.

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Amendment A

Please replace paragraph [0015] with the following amended paragraph:

[0015] As another example, there is a method in which a GaAs layer or an AlGaAs layer is grown, which can be doped with a high concentration (>1020 atoms/cm3), between the p-type nitride semiconductor layer 500 and the p-side electrode 600 (U.S. Patent No.6,410,944). In this method, however, since the bandgap of the GaAs layer or the AlGaAs layer is smaller than that of the visible region, most. Most of light generated from the active layer 400 may be absorbed by the GaAs layer or the AlGaAs layer. Therefore, this method has limited application fields.

Please replace paragraph [0046] with the following amended paragraph:

[0046] Table 1 shows electrical characteristics of a device, which is formed by growing silicon carbide of about 20Å in thickness, which is doped with a high concentration, on a common GaNbased light emitting device. At this time, an electrode used was an ITO(Indium Tin Oxide) electrode. From Table 1, it can be seen that a case where a silicon carbide layer is formed has a low contact resistance value compared to a case where an electrode is formed on p-type GaN without silicon carbide layer.